

EAS I - [Untitled1:1]

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Buttons: Refresh, Print, Download, Upload, Post

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Default operator: GR

(transistor or amplifier) and (control or controls) adj3 (channel adj length or channel adj width)

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		Document ID	Issue Date	Pages	Title	Current DR	Current XRef	Retrieval Class	Inventor	SS	CC	CP	AS	
1	<input type="checkbox"/>	US 20040174762 A1	20040909	7	Deep power down switch for memory device	365/226			Suh, Jungwon	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 20040174349 A1	20040909	40	Driving circuits for displays	345/204			Ubsch, Frank Robert et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 20040170050 A1	20040902	27	Semiconductor integrated circuit device with improved storage MOSFET arrangement	365/149			Itoh, Kiyoo et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 20040166634 A1	20040826	11	Array architecture and process flow of nonvolatile memory devices for mass storage applications	438/262			Lee, Peter W. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 20040165459 A1	20040826	12	Array architecture and process flow of nonvolatile memory devices for mass storage applications	365/200			Lee, Peter W. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 20040152274 A1	20040805	7	Methods for manufacturing semiconductor devices	438/300	438/197; 438/299; 438/301; 438/266;		Park, Cheolsoo	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 20040142523 A1	20040722	15	Method of forming vertical mosfet with ultra-low on-resistance and low gate charge	438/197	438/197; 438/270; 438/299		Bencuya, Izak et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	US 20040140830 A1	20040722	18	Class AB digital to analog converter/line driver	327/65			Mukder, Jan et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
9	<input type="checkbox"/>	US 20040132256 A1	20040708	12	MOS transistor having a recessed gate electrode and fabrication method thereof	438/296	438/197; 438/270; 438/261		Kim, Jae-Hun et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
10	<input type="checkbox"/>	US 20040132250 A1	20040708	75	Preventing dielectric thickening over a gate area of a transistor	438/264	257/E21.682; 257/E27.103; 257/E29.120;		Hazani, Emanuel	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
11	<input type="checkbox"/>	US 20040119100 A1	20040624	12	DENSE DUAL-PLANE DEVICES	257/204	257/206; 257/351; 438/197		Nowak, Edward J. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

Buttons: Details, HTML

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